Unit: mm

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type ($L^2-\pi$ -MOSV)

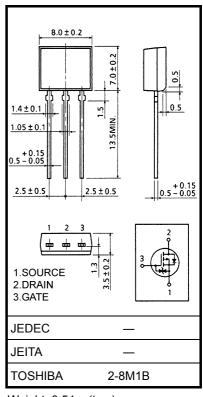
2SJ525

Chopper Regulator, DC–DC Converter and Motor Drive Applications

- 4-V gate drive
- Low drain-source ON resistance $: R_{DS} (ON) = 0.1 \Omega (typ.)$
- High forward transfer admittance $|Y_{fs}| = 4.5 \text{ S (typ.)}$
- Low leakage current $: I_{DSS} = -100 \ \mu A \ (max) \ (V_{DS} = -30 \ V)$
- Enhancement mode $: V_{th} = -0.8 \sim -2.0 \text{ V} (V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | | Symbol | Rating | Unit | |
|--|----------------|------------------|---------|------|--|
| Drain-source voltage | | V _{DSS} | -30 | V | |
| Drain-gate voltage (R _{GS} = 20 kΩ) | | V _{DGR} | -30 | V | |
| Gate-source voltage | | V _{GSS} | ±20 | V | |
| Drain current | DC (Note 1) | I _D | -5 | А | |
| | Pulse (Note 1) | I _{DP} | -20 | А | |
| Drain power dissipation | n (Ta = 25°C) | PD | 1.3 | W | |
| Single pulse avalanche energy (Note 2) | | E _{AS} | 517 | mJ | |
| Avalanche current | | I _{AR} | -5 | А | |
| Repetitive avalanche energy (Note 3) | | E _{AR} | 0.13 | mJ | |
| Channel temperature | | T _{ch} | 150 | °C | |
| Storage temperature range | | T _{stg} | -55~150 | °C | |



Weight: 0.54 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|--|------------------------|------|--------|
| Thermal resistance, channel to ambient | R _{th (ch−a)} | 96.1 | °C / W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD} = -25 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 14.84 mH, $R_G = 25 \Omega$, $I_D = -5 \text{ A}$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.

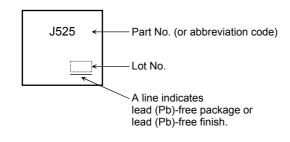
Electrical Characteristics (Ta = 25°C)

| Charac | teristics | Symbol | Test Condition | Min | Тур. | Max | Unit | |
|---|---------------|----------------------|---|------|------|------|------|--|
| Gate leakage cu | rrent | I _{GSS} | V _{GS} = ±16 V, V _{DS} = 0 V | | _ | ±10 | μA | |
| Drain cut-off cu | rrent | I _{DSS} | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$ | _ | _ | -100 | μA | |
| Drain−source br voltage | eakdown | V (BR) DSS | I _D = -10 mA, V _{GS} = 0 V | -30 | _ | _ | V | |
| Gate threshold v | voltage | V _{th} | $V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA}$ | -0.8 | _ | -2.0 | V | |
| Drain-source ON resistance | | R _{DS (ON)} | V_{GS} = -4 V, I _D = -2.5 A | — | 0.17 | 0.2 | Ω | |
| | | | V _{GS} = -10 V, I _D = -2.5 A | _ | 0.1 | 0.12 | 12 | |
| Forward transfer | admittance | Y _{fs} | V _{DS} = -10 V, I _D = -2.5 A | 2.0 | 4.5 | _ | S | |
| Input capacitance | e | C _{iss} | | | 850 | _ | pF | |
| Reverse transfer capacitance | | C _{rss} | V_{DS} = -10 V, V_{GS} = 0 V, f = 1 MHz | _ | 250 | _ | | |
| Output capacitance | | Coss | | | 330 | _ | | |
| Switching time | Rise time | tr | $V_{GS} = 10V$ $V_{GS} = 10V$ $V_{DD} = -15V$ $Duty \le 1\%, t_{W} = 10\mu s$ | _ | 50 | _ | | |
| | Turn-on time | t _{on} | | _ | 75 | _ | • ns | |
| | Fall time | t _f | | | 20 | _ | | |
| | Turn-off time | t _{off} | | | 95 | _ | | |
| Total gate charge (Gate-source plus gate-drain) | | Qg | V _{DD} ≈ −24 V, V _{GS} = −10 V, | _ | 27 | _ | | |
| Gate-source charge | | Q _{gs} | $I_{\rm D} = -5 \text{ A}$ | | 19 | _ | nC | |
| Gate-drain ("miller") charge | | Q _{gd} | | | 8 | — | | |

Source–Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--|------------------|---|-----|------|-----|------|
| Continuous drain reverse current (Note 1) | I _{DR} | — | - | _ | -5 | А |
| Pulse drain reverse current (Note 1) | I _{DRP} | — | - | - | -20 | A |
| Forward voltage (diode) | V _{DSF} | I _{DR} = -5 A, V _{GS} = 0 V | _ | _ | 1.7 | V |
| Reverse recovery time | t _{rr} | I _{DR} = -5 A, V _{GS} = 0 V | _ | 60 | — | ns |
| Reverse recovery charge | Q _{rr} | dI _{DR} / dt = 50 A / μs | _ | 56 | _ | nC |

Marking



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20070701-EN

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